

TOSHIBA**TC74HC390AP/AF/AFN**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

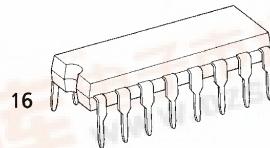
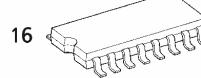
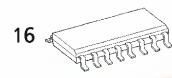
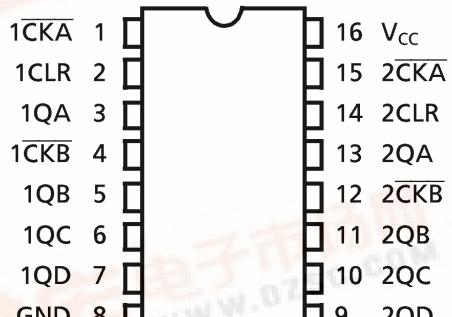
TC74HC390AP, TC74HC390AF, TC74HC390AFN**DUAL DECADE COUNTER**

The TC74HC390A is a high speed CMOS DUAL DECADE COUNTER fabricated with silicon gate C²MOS technology. It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation. It consists of two independent 4-bit counters, each composed of a divide - by - two and a divide - by - five counter. The divide - by - two counter is incremented on the negative going transition of clock A(\overline{CKA}). The divided - by - five counter is incremented on the negative going transition of clock B(\overline{CKB}). The counter can be cascaded to form decade, bi-quinary, or various combinations up to a divide - by - 100 counter. When the CLR input is set high, the Q outputs are set to low independent of the clock inputs. All inputs are equipped with protection circuits against static discharge or transient excess voltage.

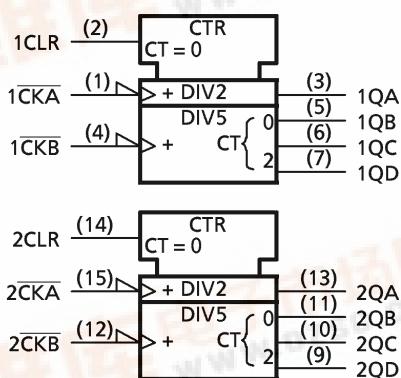
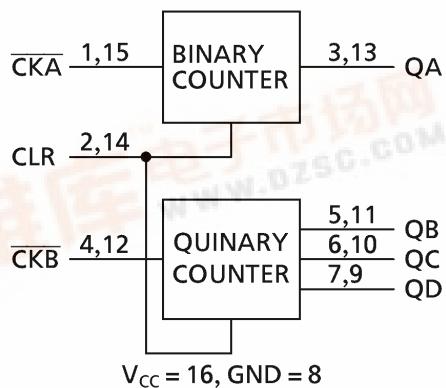
FEATURES:

- High Speed..... $f_{MAX} = 84\text{MHz}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}(\text{Min.})$
- Output Drive Capability.....10 LSTTL Loads
- Symmetrical Output Impedance..... $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range..... $V_{CC}(\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS390

(Note) The JEDEC SOP (FN) is not available in Japan.

P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)FN (SOL16-P-150-1.27)
Weight : 0.13g (Typ.)**PIN ASSIGNMENT**

(TOP VIEW)

IEC LOGIC SYMBOL**BLOCK DIAGRAM**

961001EBA2

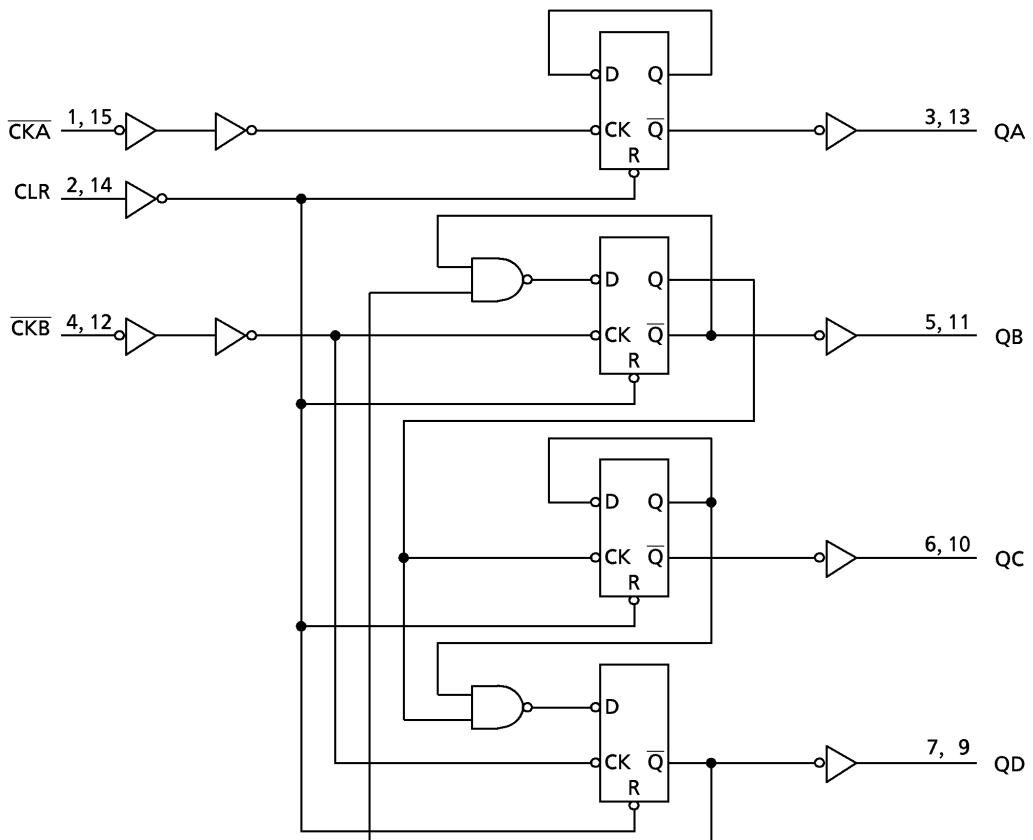
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TRUTH TABLE

INPUTS			OUTPUTS			
CKA	CKB	CLR	QA	QB	QC	QD
X	X	H	L	L	L	L
—	X	L	BINARY COUNT UP			
X	—	L	QUINARY COUNT UP			

X : Don't Care

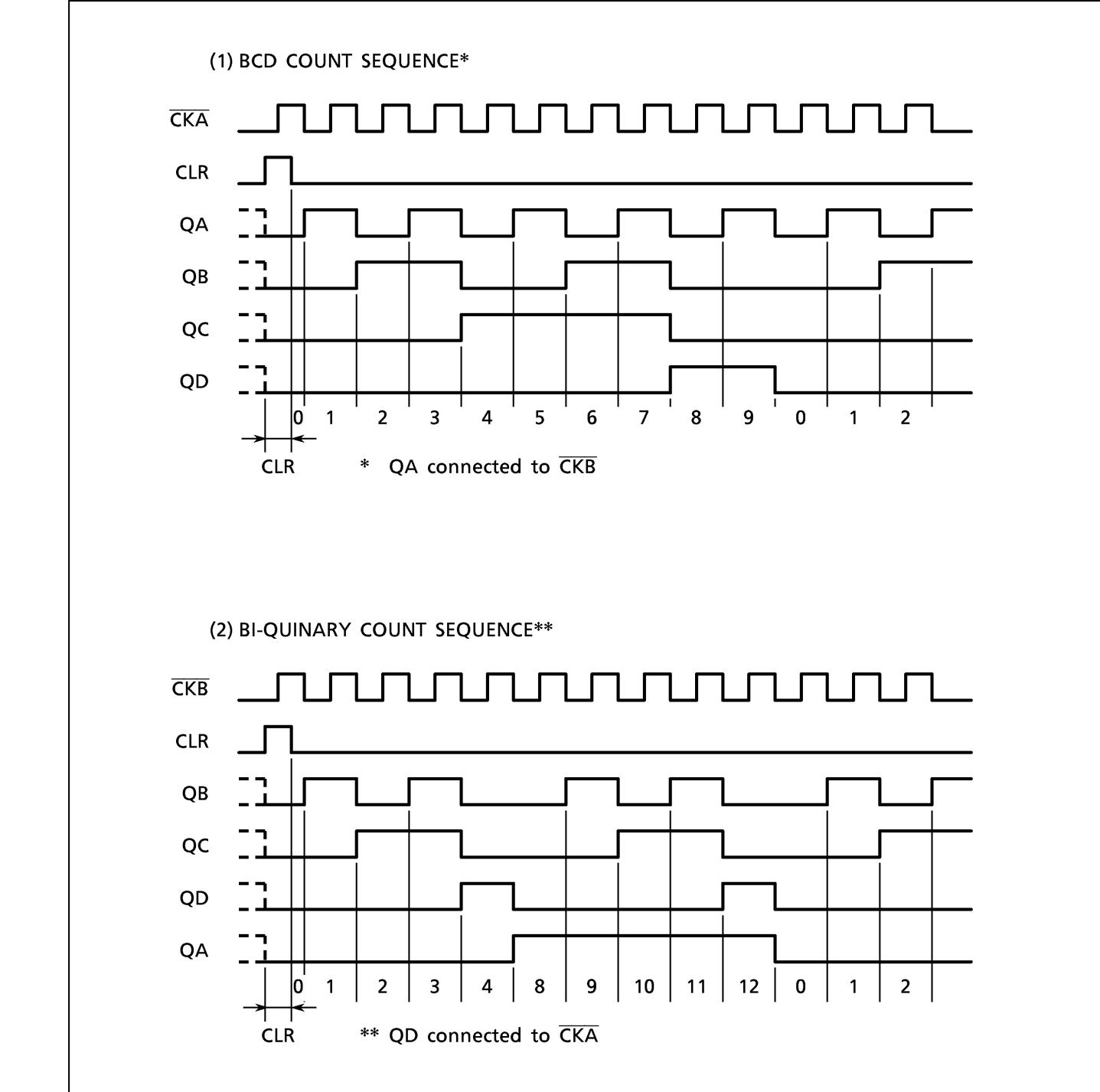
SYSTEM DIAGRAM (1/2 package)



961001EBA2'

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TIMING CHART



ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} /Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{STG}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0	1.50	—	—	1.50	—	V
			4.5	3.15	—	—	3.15	—	
			6.0	4.20	—	—	4.20	—	
Low - Level Input Voltage	V_{IL}		2.0	—	—	0.50	—	0.50	V
			4.5	—	—	1.35	—	1.35	
			6.0	—	—	1.80	—	1.80	
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0	1.9	2.0	—	1.9	V
			$I_{OH} = -4\text{ mA}$	4.5	4.4	4.5	—	4.4	
			$I_{OH} = -5.2\text{ mA}$	6.0	5.9	6.0	—	5.9	
				4.5	4.18	4.31	—	4.13	
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	6.0	5.68	5.80	—	5.63	V
			$I_{OL} = 4\text{ mA}$	2.0	—	0.0	0.1	—	
			$I_{OL} = 5.2\text{ mA}$	4.5	—	0.17	0.26	—	
				6.0	—	0.18	0.26	—	
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0	

TIMING REQUIREMENTS (Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$		$T_a = -40\text{--}85^\circ\text{C}$	UNIT
				TYP.	LIMIT	LIMIT	
Minimum Pulse Width ($\overline{\text{CK}}$)	$t_{W(H)}$		2.0	—	75	95	ns
	$t_{W(L)}$		4.5	—	15	19	
			6.0	—	13	16	
Minimum Pulse Width ($\overline{\text{CLR}}$)	$t_{W(H)}$		2.0	—	75	95	ns
			4.5	—	15	19	
			6.0	—	13	16	
Minimum Removal Time	t_{rem}		2.0	—	25	30	
			4.5	—	5	6	
			6.0	—	5	5	
Clock Frequency ($\overline{\text{CKA}}$)	f		2.0	—	6	5	MHz
			4.5	—	32	26	
			6.0	—	38	31	
Clock Frequency ($\overline{\text{CKB}}$)	f		2.0	—	6	5	MHz
			4.5	—	31	25	
			6.0	—	36	29	

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Output Transition Time	t_{TLH}		—	4	8	ns	
	t_{THL}						
Propagation Delay Time ($\overline{\text{CKA}} - \text{QA}$)	t_{pLH}		—	10	20		
	t_{pHL}						
Propagation Delay Time ($\overline{\text{CKA}} - \text{QC}$)	t_{pLH}	QA connected to $\overline{\text{CKB}}$	—	29	51	ns	
	t_{pHL}						
Propagation Delay Time ($\overline{\text{CKB}} - \text{QB}, \text{QD}$)	t_{pLH}		—	12	22		
	t_{pHL}						
Propagation Delay Time ($\overline{\text{CKB}} - \text{QC}$)	t_{pLH}		—	17	32		
	t_{pHL}						
Propagation Delay Time ($\overline{\text{CLR}} - \text{Qn}$)	t_{pHL}		—	12	26		
Maximum Clock Frequency ($\overline{\text{CKA}}$)	f_{MAX}		35	84	—	MHz	
Maximum Clock Frequency ($\overline{\text{CKB}}$)	f_{MAX}		33	65	—		

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	Ta = 25°C			Ta = -40~85°C		UNIT	
				MIN.	TYP.	MAX.	MIN.	MAX.		
Output Transition Time	t_{TLH}		2.0	—	30	75	—	95	ns	
	t_{THL}		4.5	—	8	15	—	19		
	t_{THL}		6.0	—	7	13	—	16		
Propagation Delay Time (\overline{CKA} –QA)	t_{PLH}		2.0	—	39	120	—	150	ns	
	t_{PHL}		4.5	—	13	24	—	30		
	t_{PHL}		6.0	—	11	20	—	26		
Propagation Delay Time (\overline{CKA} –QC)	t_{PLH}	QA connected to \overline{CKB}	2.0	—	102	290	—	365	ns	
	t_{PHL}		4.5	—	34	58	—	73		
	t_{PHL}		6.0	—	29	49	—	62		
Propagation Delay Time (\overline{CKB} –QB, QD)	t_{PLH}		2.0	—	45	130	—	165		
	t_{PHL}		4.5	—	15	26	—	33		
	t_{PHL}		6.0	—	13	22	—	28		
Propagation Delay Time (\overline{CKB} –QC)	t_{PLH}		2.0	—	63	185	—	230		
	t_{PHL}		4.5	—	21	37	—	46		
	t_{PHL}		6.0	—	18	31	—	39		
Propagation Delay Time (CLR–Qn)	t_{PHL}		2.0	—	45	150	—	190	MHz	
	t_{PHL}		4.5	—	15	30	—	38		
	t_{PHL}		6.0	—	13	26	—	32		
Maximum Clock Frequency (\overline{CKA})	f_{MAX}		2.0	6	20	—	5	—	MHz	
	f_{MAX}		4.5	32	77	—	26	—		
	f_{MAX}		6.0	38	90	—	31	—		
Maximum Clock Frequency (\overline{CKB})	f_{MAX}		2.0	6	15	—	5	—		
	f_{MAX}		4.5	32	60	—	25	—		
	f_{MAX}		6.0	36	70	—	29	—		
Input Capacitance	C_{IN}				—	5	10	—	10	pF
Power Dissipation Capacitance	C_{PD} (1)				—	44	—	—	—	

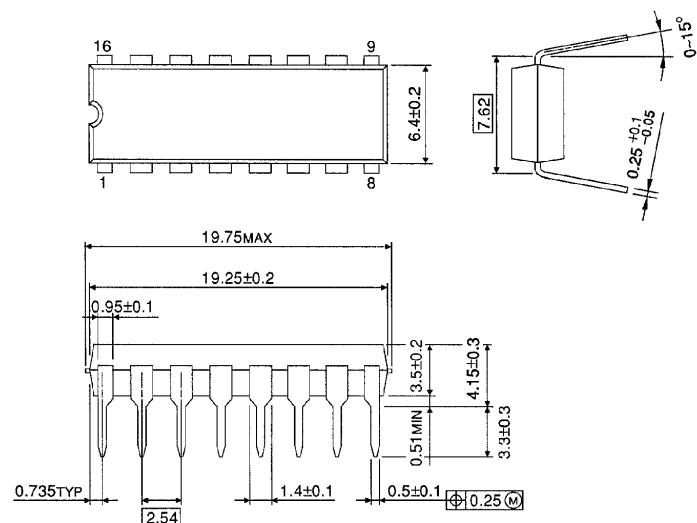
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC}(\text{opr}) = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/2 \text{ (per Counter)}$$

DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

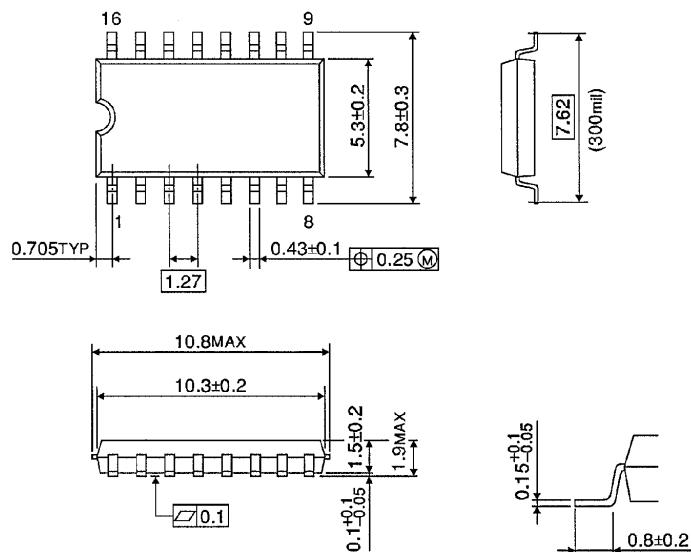
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

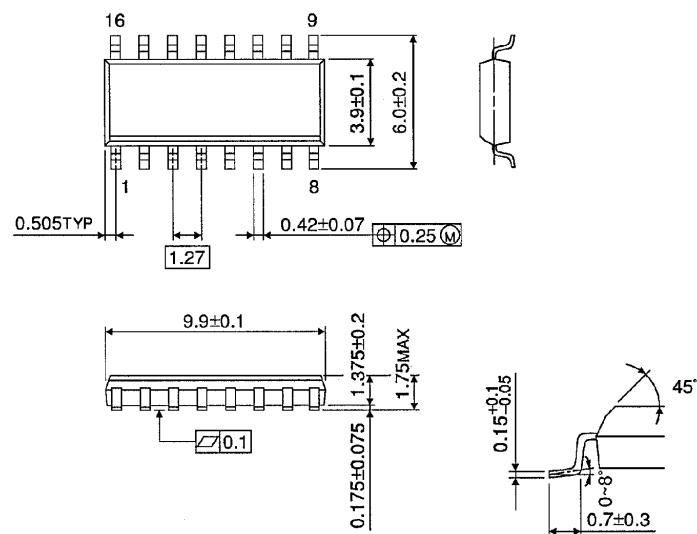


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150 -1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)